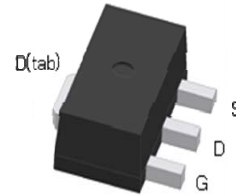


P-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	-30V
R _{DS(on)} (MAX.)	50mΩ
I _D	-4A



Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _A = 25 °C	I _D	-4	A
	T _A = 100 °C		-3	
Pulsed Drain Current ¹		I _{DM}	-16	
Power Dissipation	T _A = 25 °C	P _D	1.47	W
	T _A = 70 °C		0.94	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		18	°C / W
Junction-to-Ambient ³	R _{θJA}		85	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³85°C / W when mounted on a 1 in² pad of 2 oz copper.

ELECTRICAL CHARACTERISTICS ($T_c = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

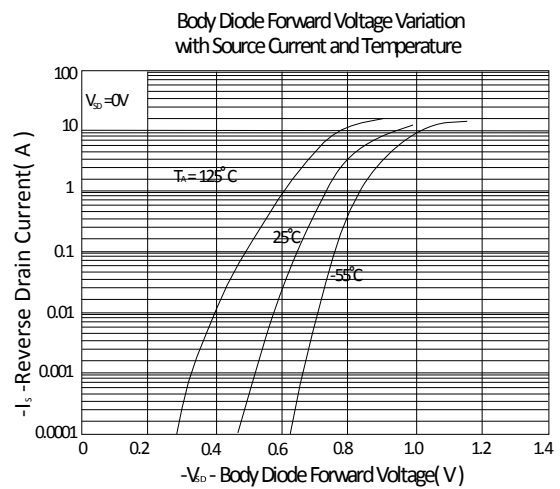
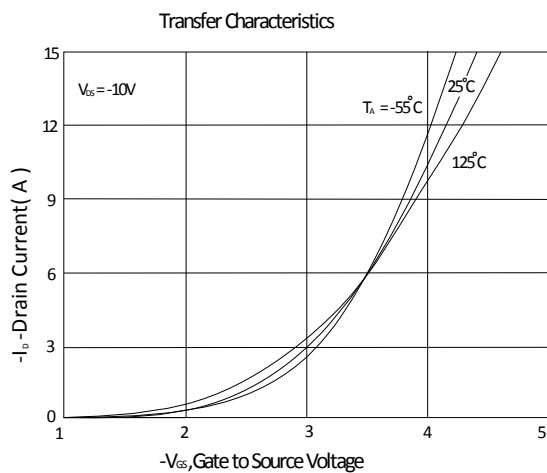
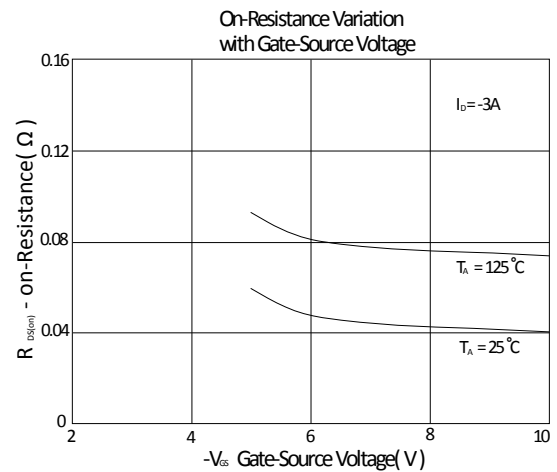
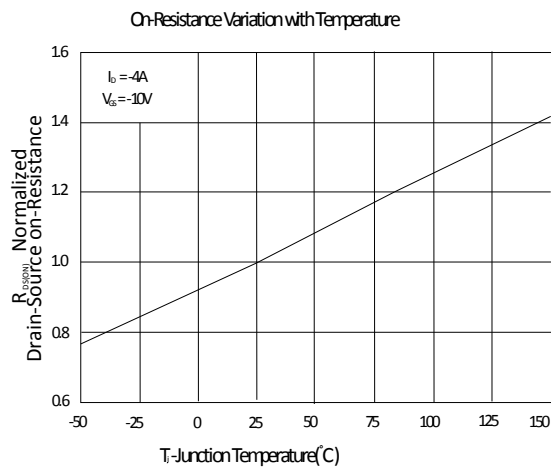
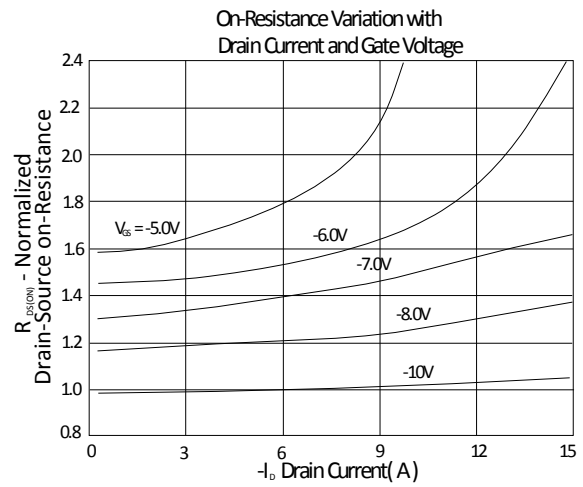
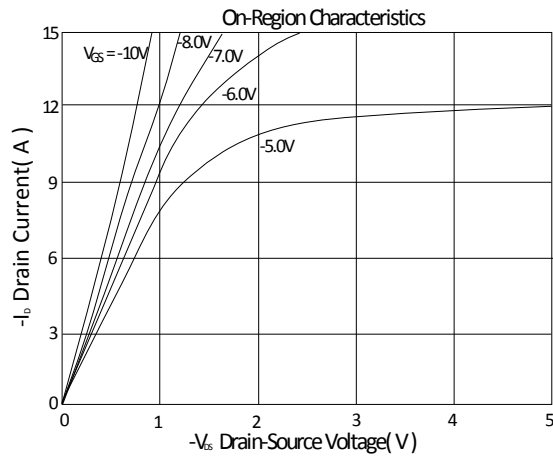
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$			-10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = -5V, V_{GS} = -10V$	-4			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -4A$		43	50	m Ω
		$V_{GS} = -5V, I_D = -3A$		60	75	
Forward Transconductance ¹	g_{fs}	$V_{DS} = -5V, I_D = -4A$		16		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -15V, f = 1MHz$		820		pF
Output Capacitance	C_{oss}			122		
Reverse Transfer Capacitance	C_{rss}			97		
Total Gate Charge ^{1,2}	Q_g	$V_{DS} = -15V, V_{GS} = 10V,$ $I_D = -4A$		9		nC
Gate-Source Charge ^{1,2}	Q_{gs}			2.2		
Gate-Drain Charge ^{1,2}	Q_{gd}			2.5		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$	$V_{DS} = -15V,$ $I_D = -1A, V_{GS} = -10V, R_{GS} = 6\Omega$		5.5		nS
Rise Time ^{1,2}	t_r			10		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			18		
Fall Time ^{1,2}	t_f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)						
Continuous Current	I_S				-2.3	A
Pulsed Current ³	I_{SM}				-9.2	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			-1.3	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, di_F/dt = 100A / \mu S$		15		nS
Reverse Recovery Charge	Q_{rr}			8		nC

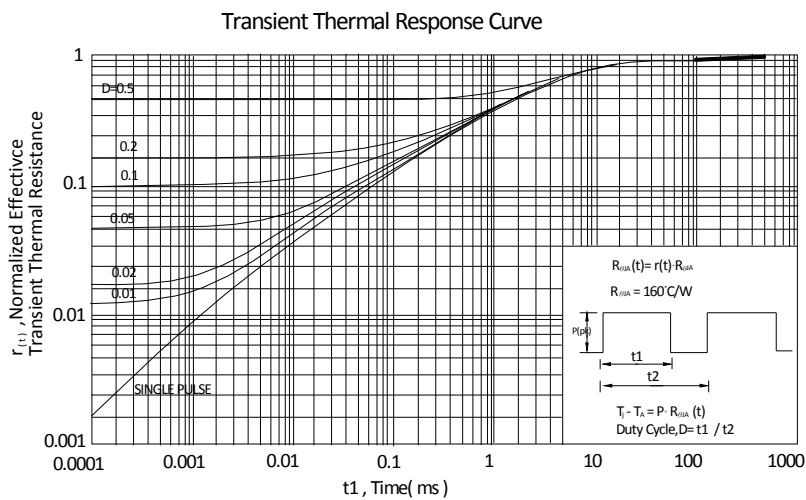
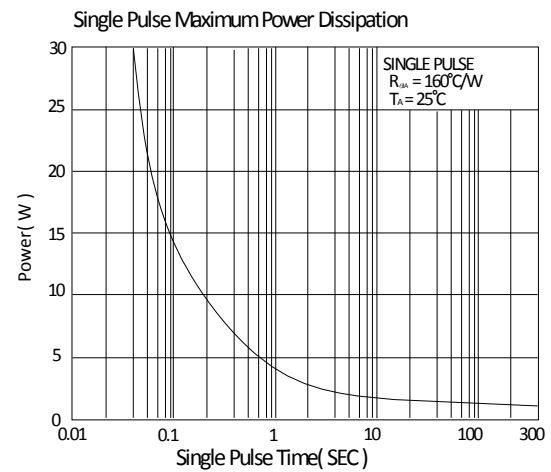
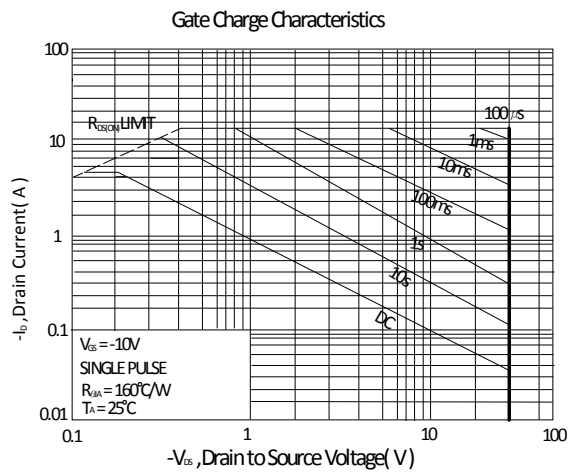
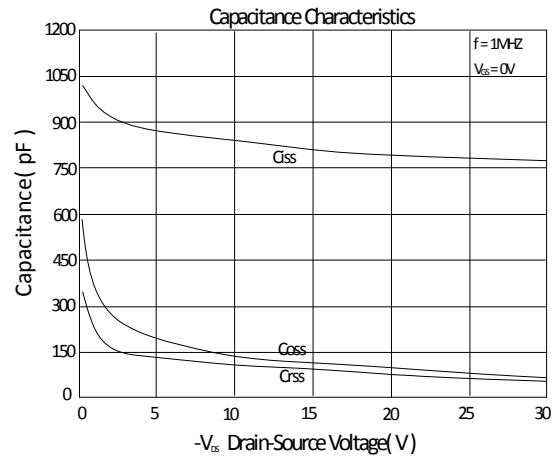
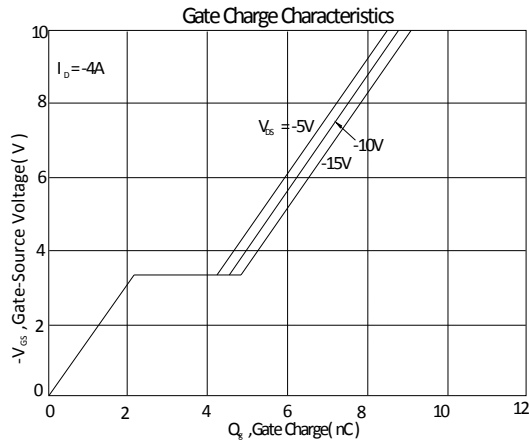
¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

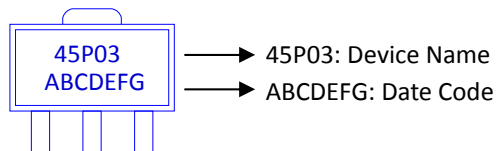
TYPICAL CHARACTERISTICS



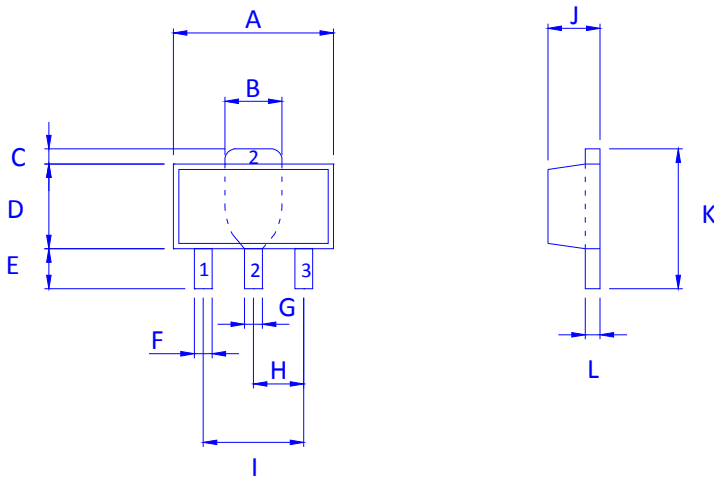


Ordering & Marking Information:

Device Name: LB45P03J for SOT-89



Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K	L
in.	4.30	1.60	0.40	2.40	0.80	0.40	0.40	1.40	2.80	1.30	3.80	0.30
Typ.												
Max.	4.70	1.80	0.60	2.60	1.40	0.50	0.60	1.60	3.20	1.70	4.60	0.50

Footprint

